BRGB20N65FL

Rev.A Mar.-2026

DATA SHEET

/ Descriptions

TO-220FL ṂṂ Ł ʌ ɻ ᴥ ‖ ὐ ч ᄀ

Insulated-Gate Bipolar Transistor in a TO-220FL Plastic Package.

/ Features

650V/20A $V_{CE(SAT)}$= 1.45V(typ.) @I_C= 20A

Ḥ ‖ ɔ U Low gate charge

Trench FS ΄H Trench FS Technology

RoHS ғ β RoHS product

/ Applications

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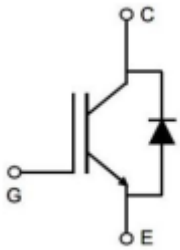
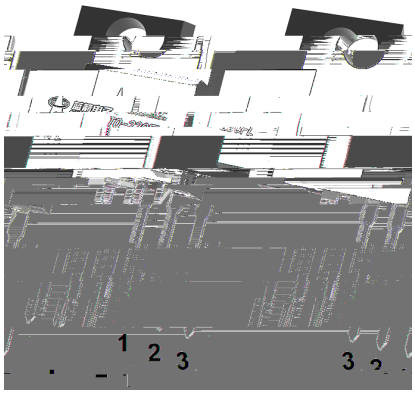
General purpose inverters,UPS.

/ Equivalent Circuit



/ Pinning



PIN1 χ G PIN 2 χ C PIN 3 χ E

/ Marking

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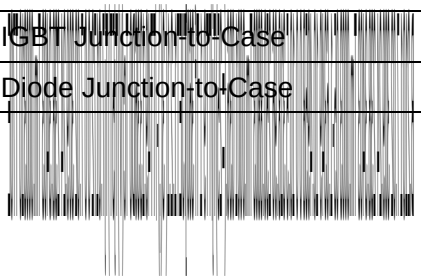
See Marking Instructions.

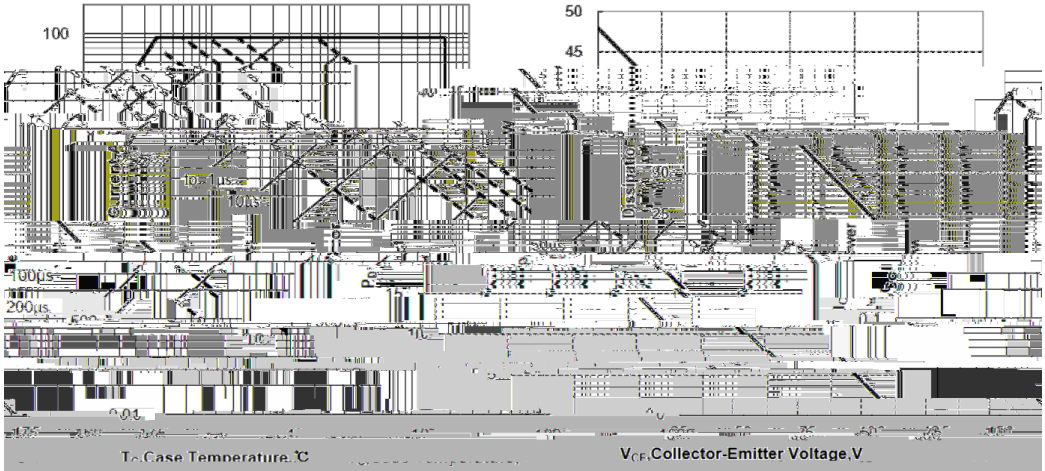
v ‘Ω Parameter		↑ N Symbol	‘Ω Ö Rating	D Ђ Unit
Collector-Emitter Voltage		V_{CES}	650	V
Continuous Collector Current	T_C=+25	I_C	40	A
	T_C=+100		20	A
Pulsed Collector Current , Limited by T_{Jmax}		I_{CM}	80	A
Continuous Diode Forward Current	T_C=+25	I_F	40	A
	T_C=+100		20	A
Surge non repetitive forward current tp= 8.3 ms sinusoidal		I_{FSM}	120	A
Gate-Emitter Voltage		V_{GE}	± 30	V
Power Dissipation	T_C=+25	P_D	48	W
Operating and Storage Temperature Range		T_{STG}	-55 to +175	
Operating Temperature Range		T_J	-55 to +175	
Maximum Junction-to-Ambient		$R_{\theta JA}$	78	/W
Maximum IGBT Junction-to-Case		$R_{\theta JC}$	3.10	/W
Maximum Diode Junction-to-Case		$R_{\theta JC}$	4.12	/W



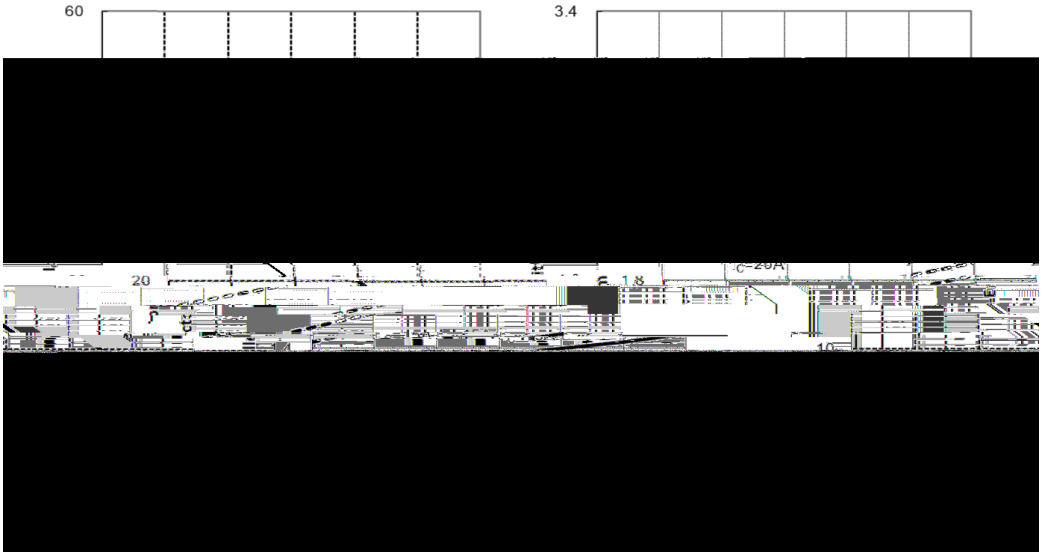
v ‘Ω Parameter	↑ N Symbol	‡ ; † Ţ Test Conditions	ω ņ Ö Min	Ɛ ʒ Ö Typ	ω ² Ö Max	D Ђ Unit
Collector-Emitter Breakdown Voltage	BV_{CES}	I_C=250uA, V_{GE}=0V	650			V
Zero Gate Voltage Collector current	I_{CES}	V_{CE}=650V, V_{GE}=0V 194.00=2558 0 Tc T_J=25			35	uA

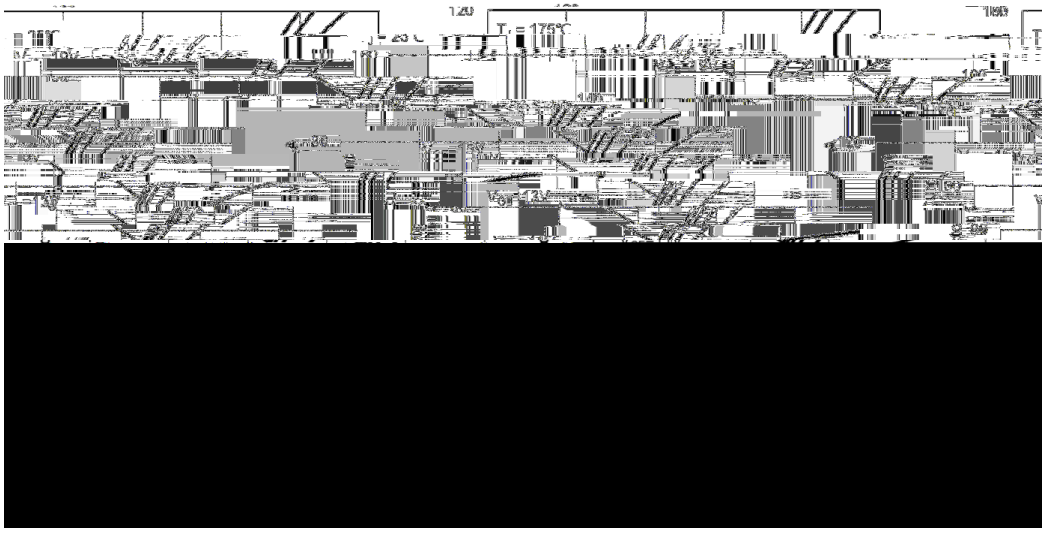
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=20A	T_J=25		1.45	1.82	V
			T_J=125		1.68		
			T_J=175		1.93		
Diode Forward Voltage	V_F	V_{GE}=0V, I_F=20A	T_J=25		1.40	1.84	V
			T_J=125		1.24		
			T_J=175		1.14		
Input Capacitance	C_{ies}	V_{GE}=0V, V_{CE}=25V, f=1MHz,T_J=25			1420		pF
Output Capacitance	C_{oes}				72		pF

/ Electrical Characteristic Curve

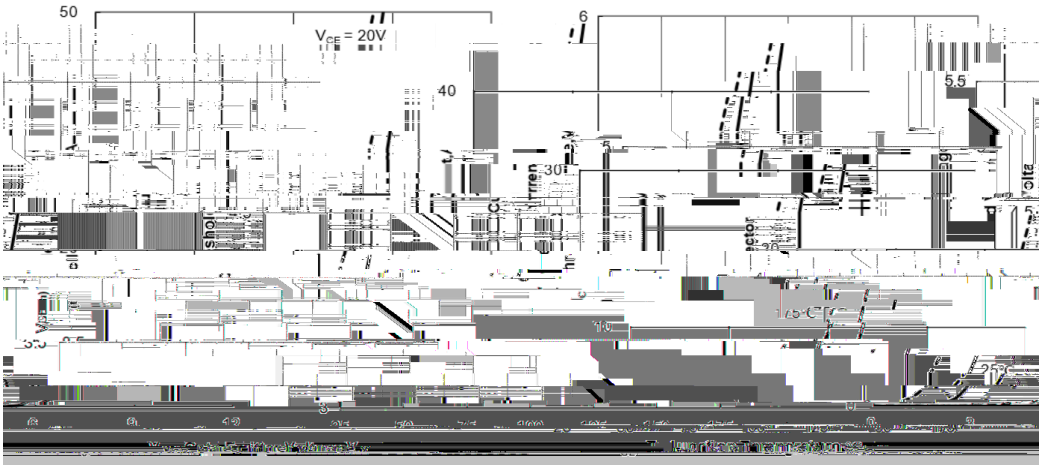


erating Area Figure 2. Power Dissipation vs Case Temperature Figure 1. Forward Bias Safe Op





/ Electrical Characteristic Curve



igure 8. Typical Gate-Emitter Threshold Voltage vs Junction Temperature

Figure 7. Typical Transfer Characteristics

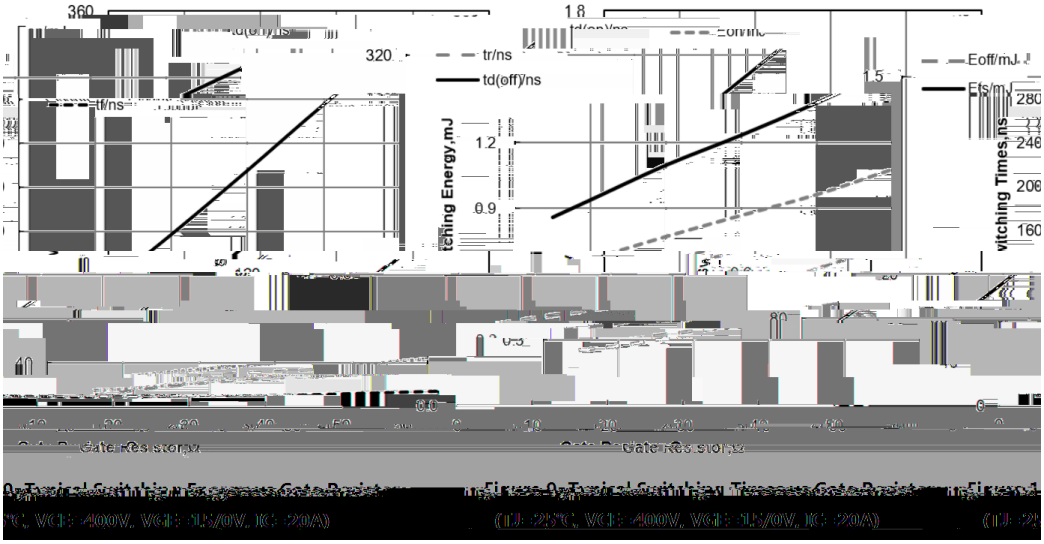
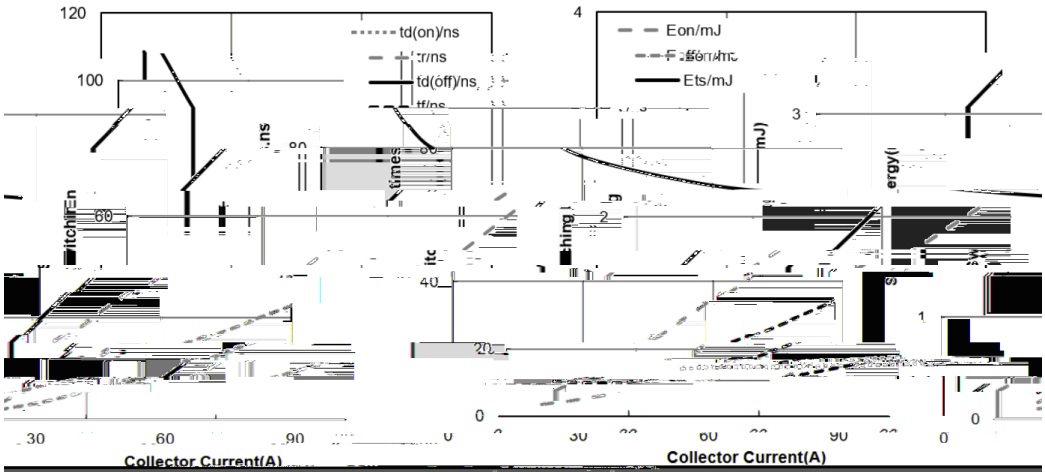


Figure 9. Typical Switching Times vs Gate Resistor (TC, VCE: 400V, VGE: 15/0V, IC: 20A)

Figure 10. Typical Switching Times vs Gate Resistor (TJ: 25°C, VCE: 400V, VGE: 15/0V, IC: 20A)

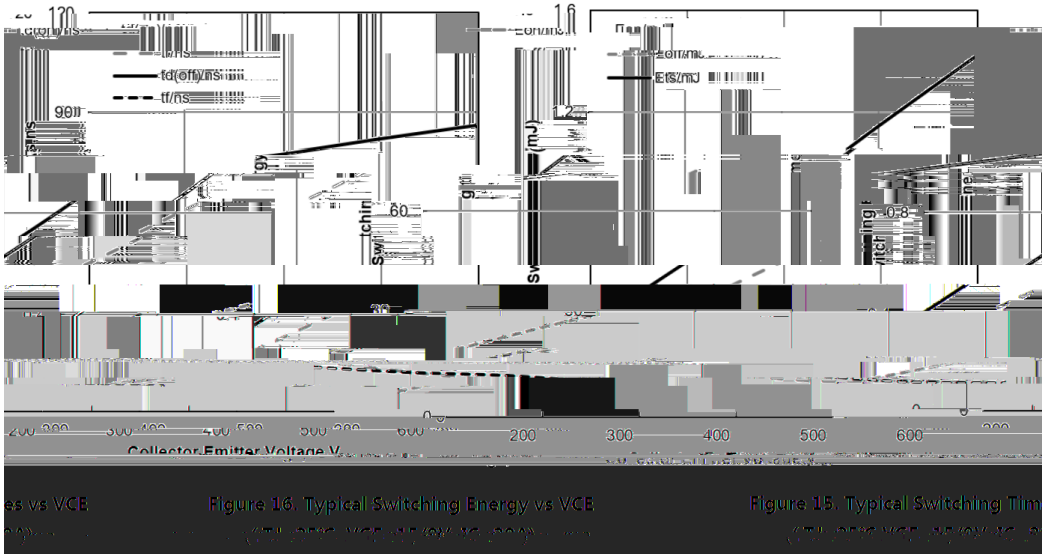
/ Electrical Characteristic Curve



ical Switching Times vs Collector 25°C, VCE=400V, VGE=15/0V)

Figure 14. Typical Switching Energy vs Collector Current (TJ=25°C, VCE=400V, VGE=15/0V)

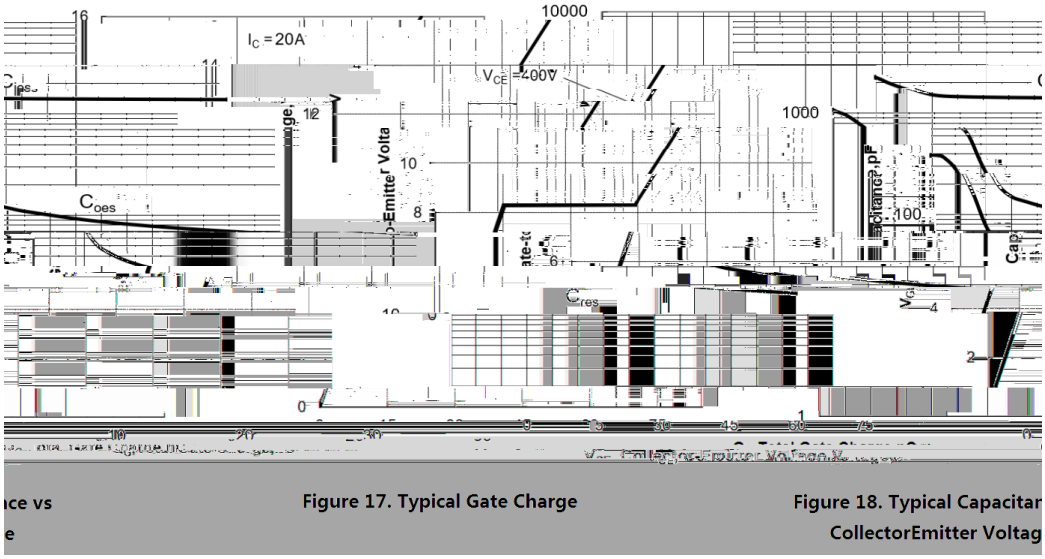
Figure 13. Typ Current (TJ=



es vs VCE

Figure 16. Typical Switching Energy vs VCE

Figure 15. Typical Switching Tim

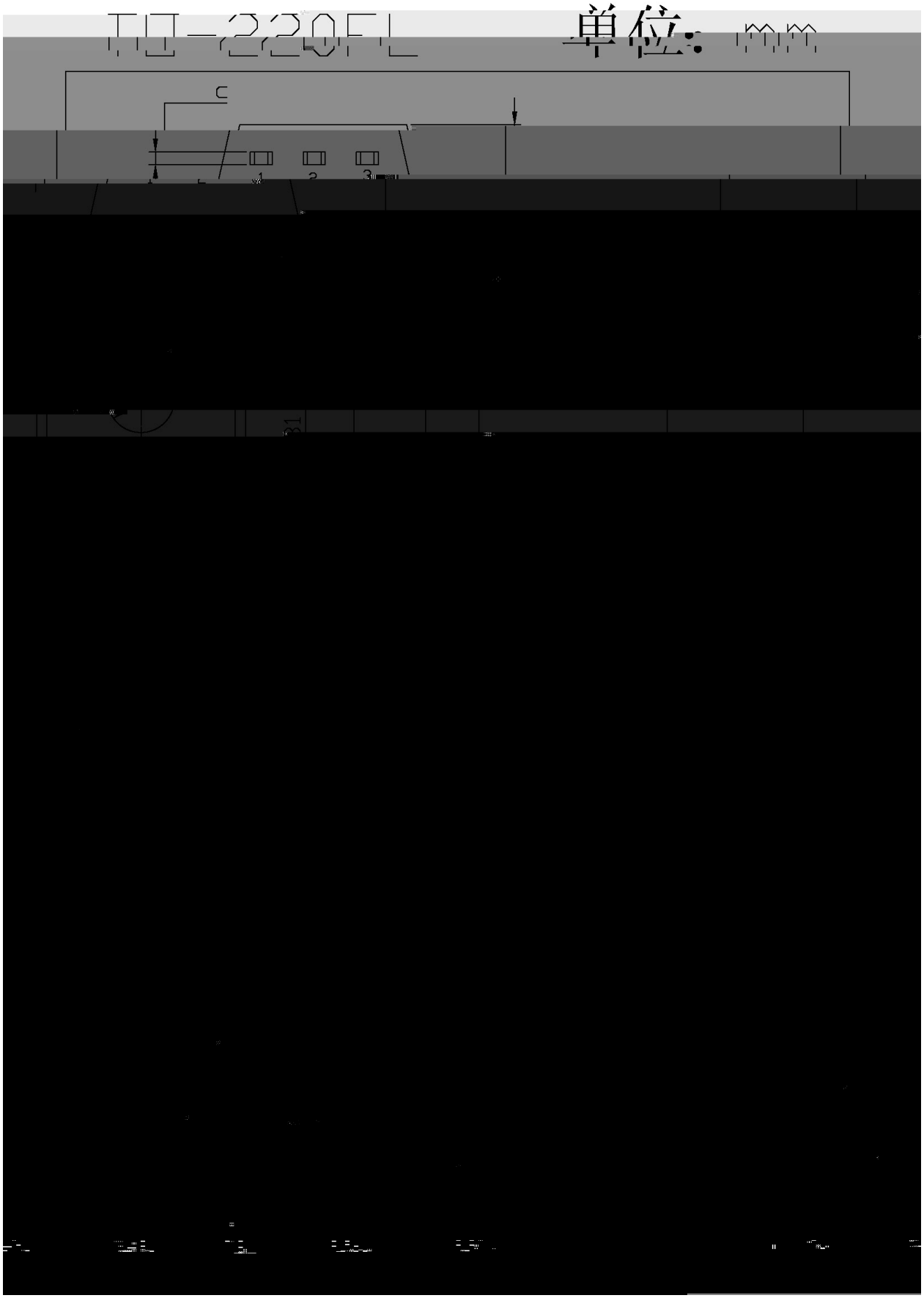


nce vs e

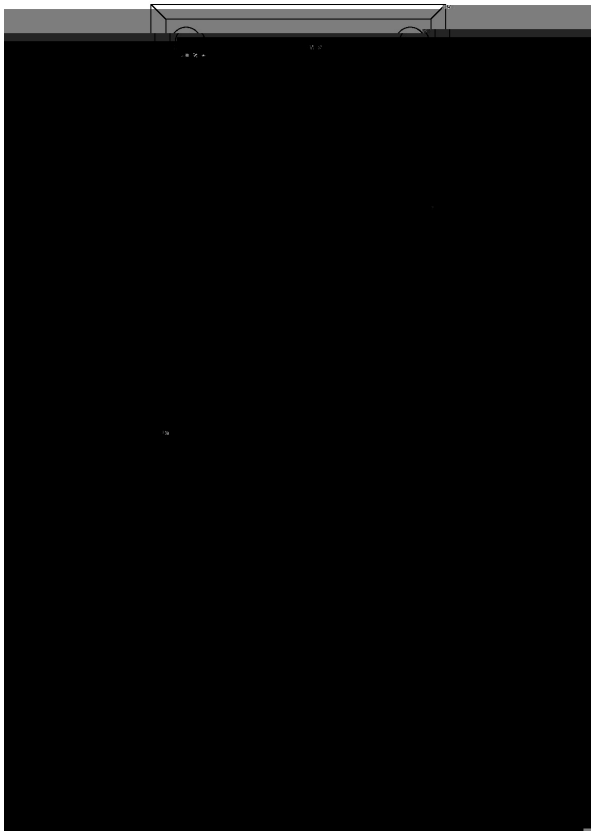
Figure 17. Typical Gate Charge

Figure 18. Typical Capacitar CollectorEmitter Voltag

/ Package Dimensions



/ Marking Instructions



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